The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-32. (Canceled)

33. (Currently Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a crystalline semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to a semiconductor film;

forming a gate electrode over a portion of the crystalline semiconductor film which is included in an element-forming region; and

forming an impurity region in the crystalline semiconductor film using the gate electrode as a mask,

wherein a scanning direction of the beam changes outside [[an]] the element-forming region ~~formed in the crystalline semiconductor film~~.

34. (Currently Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a crystalline semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to a semiconductor film;

forming a gate electrode over a portion of the crystalline semiconductor film which is included in an element-forming region; and

forming an impurity region in the crystalline semiconductor film using the gate electrode as a mask,

wherein the beam ~~is irradiated to an outside of~~ starts irradiation from outside the element-forming region ~~formed in the crystalline semiconductor film when a scanning of~~

~~the beam starts or the scanning of the beam ends~~ or ends irradiation outside the element-forming region.

35. (Previously Presented) A method for manufacturing a thin film transistor according to claim 33,

wherein the scanning of the energy beam is performed by using a galvanometer mirror or a polygon mirror.

36. (Previously Presented) A method for manufacturing a thin film transistor according to claim 34,

wherein the scanning of the energy beam is performed by using a galvanometer mirror or a polygon mirror.

37. (Original) A method for manufacturing a thin film transistor according to claim 33,

wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO_4 laser, a YAG laser, a YLF laser, a $YAlO_3$ laser, and an Ar laser.

38. (Original) A method for manufacturing a thin film transistor according to claim 34,

wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO_4 laser, a YAG laser, a YLF laser, a $YAlO_3$ laser, and an Ar laser.

39. (Original) A method for manufacturing a thin film transistor according to claim 33,

wherein the element-forming region is a region where a display device or an integrated circuit is formed.

40. (Original) A method for manufacturing a thin film transistor according to claim 34,

wherein the element-forming region is a region where a display device or an integrated circuit is formed.

41. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over a substrate;

crystallizing the semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to the semiconductor film;

forming a plurality of semiconductor islands using the crystallized semiconductor film;

forming a first circuit using one of the plurality of semiconductor islands over the substrate; and

forming a second circuit using another one of the plurality of semiconductor islands over the substrate,

wherein the energy beam is irradiated [[to an]] outside [[of]] the first circuit and the second circuit while changing a scanning direction of the energy beam.

42. (Previously Presented) A method for manufacturing a semiconductor device according to claim 41,

wherein the energy beam is irradiated to a region between the first circuit and the second circuit while changing the scanning direction of the energy beam.

43.-44. (Canceled)

45. (Previously Presented) A method for manufacturing a semiconductor device according to claim 33,

wherein the semiconductor device is incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.

46. (Previously Presented) A method for manufacturing a semiconductor device according to claim 34,

wherein the semiconductor device is incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.

47. (Previously Presented) A method for manufacturing a semiconductor device according to claim 41,

wherein the semiconductor device is incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.

48. (Previously Presented) A method for manufacturing a thin film transistor according to claim 41,

wherein the scanning of the energy beam is performed by using a galvanometer mirror or a polygon mirror.

49. (Previously Presented) A method for manufacturing a thin film transistor according to claim 41,

wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO_4 laser, a YAG laser, a YLF laser, a $YAlO_3$ laser, and an Ar laser.

50. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over a substrate;

crystallizing the semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to the semiconductor film;

forming a plurality of semiconductor islands by using the crystallized semiconductor film;

forming a first circuit using one of the plurality of semiconductor islands over the substrate; and

forming a second circuit using another one of the plurality of semiconductor islands over the substrate,

wherein the energy beam ~~is irradiated to an~~ starts irradiation from outside [[of]] the first circuit and the second circuit ~~when a scanning of the beam starts or the scanning of the beam ends~~ or ends irradiation outside the first circuit and the second circuit.

51. (Currently Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a crystalline semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to a semiconductor film by moving the semiconductor film and the energy beam relatively;

forming a gate electrode over a portion of the crystalline semiconductor film which is included in an element-forming region; and

forming an impurity region in the crystalline semiconductor film using the gate electrode as a mask,

wherein a scanning direction of the beam changes outside [[an]] the element-forming region ~~formed in the crystalline semiconductor film~~.

52. (Currently Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a crystalline semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to a semiconductor film by moving the semiconductor film and the energy beam relatively;

forming a gate electrode over a portion of the crystalline semiconductor film which is included in an element-forming region; and

forming an impurity region in the crystalline semiconductor film using the gate electrode as a mask,

wherein the beam is ~~irradiated to an outside of~~ starts irradiation from outside the element-forming region or ends irradiation outside the element-forming region ~~formed in the crystalline semiconductor film when a scanning of the beam starts or the scanning of the beam ends~~.

53. (Previously Presented) A method for manufacturing a thin film transistor according to claim 50,

wherein the scanning of the energy beam is performed by using a galvanometer mirror or a polygon mirror.

54. (Previously Presented) A method for manufacturing a thin film transistor according to claim 50,

wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO_4 laser, a YAG laser, a YLF laser, a $YAlO_3$ laser, and an Ar laser.

55. (Previously Presented) A method for manufacturing a semiconductor device according to claim 50,

wherein the semiconductor device is incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.

56. (Previously Presented) A method for manufacturing a thin film transistor according to claim 51,

wherein the scanning of the energy beam is performed by using a galvanometer mirror or a polygon mirror.

57. (Previously Presented) A method for manufacturing a thin film transistor according to claim 51,

wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO_4 laser, a YAG laser, a YLF laser, a $YAlO_3$ laser, and an Ar laser.

58. (Previously Presented) A method for manufacturing a thin film transistor according to claim 51,

wherein the element-forming region is a region where a display device or an integrated circuit is formed.

59. (Previously Presented) A method for manufacturing a semiconductor device according to claim 51,

wherein the semiconductor device is incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.

60. (Previously Presented) A method for manufacturing a thin film transistor according to claim 52,

wherein the scanning of the energy beam is performed by using a galvanometer mirror or a polygon mirror.

61. (Previously Presented) A method for manufacturing a thin film transistor according to claim 52,

wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO_4 laser, a YAG laser, a YLF laser, a $YAlO_3$ laser, and an Ar laser.

62. (Previously Presented) A method for manufacturing a thin film transistor according to claim 52,

wherein the element-forming region is a region where a display device or an integrated circuit is formed.

63. (Previously Presented) A method for manufacturing a semiconductor device according to claim 52,

wherein the semiconductor device is incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.